

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC3352

DESCRIPTION

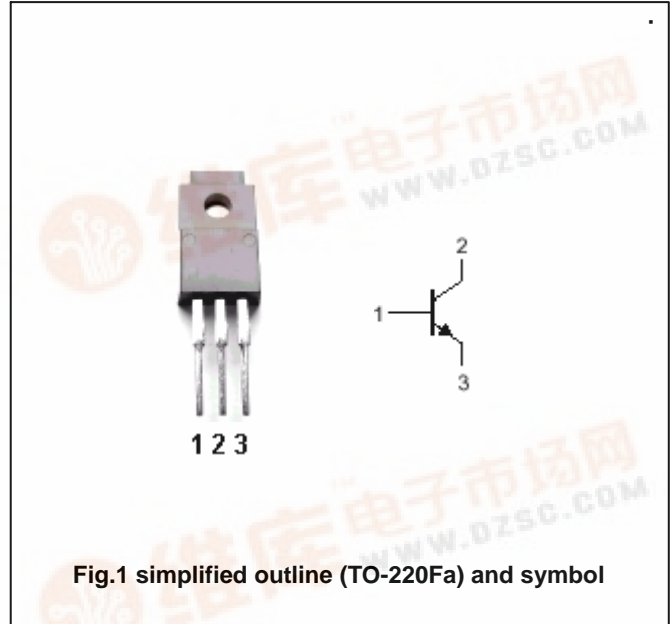
- With TO-220Fa package
- High voltage
- High speed switching

APPLICATIONS

- For high speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	800	V
V_{CEO}	Collector-emitter voltage	Open base	500	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		1.5	A
I_{CM}	Collector current-Peak		3.0	A
I_B	Base current		0.5	A
P_C	Collector power dissipation	$T_C=25$	25	W
		$T_a=25$	2	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

Silicon NPN Power Transistors

2SC3352

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA, I _B =0	500			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A; I _B =0.2A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1A; I _B =0.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =0.1A; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =1A; V _{CE} =5V	8			
f _T	Transition frequency	I _C =0.2A; V _{CE} =10V		2.5		MHz
Switching times						
t _{on}	Turn-on time	I _C =1A; I _{B1} =-I _{B2} =0.2A V _{CC} =200V			1.0	μs
t _{stg}	Storage time				3.0	μs
t _f	Fall time				1.0	μs

Silicon NPN Power Transistors

2SC3352

PACKAGE OUTLINE

